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Kind regards,

Team Nexperia

74ABT543A

Octal latched transceiver with dual enable; 3-state

Rev. 5 — 3 November 2011

Product data sheet

1. General description

The 74ABT543A high performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT543A octal registered transceiver contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch enable (LEAB, LEBA) and output enable (OEAB, OEBA) inputs are provided for each register to permit independent control of data transfer in either direction. The outputs are guaranteed to sink 64 mA.

2. Features and benefits

- Combines 74ABT245 and 74ABT373 type functions in one device
- 8-bit octal transceiver with D-type latch
- Back-to-back registers for storage
- Separate controls for data flow in each direction
- Live insertion and extraction permitted
- Output capability: +64 mA to –32 mA
- Power-up 3-state
- Power-up reset
- Latch-up protection exceeds 500 mA per JESD78B class II level A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V

3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74ABT543AD	–40 °C to +85 °C	SO24	plastic small outline package; 24 leads; body width 7.5 mm		SOT137-1
74ABT543ADB	–40 °C to +85 °C	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm		SOT340-1
74ABT543APW	–40 °C to +85 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm		SOT355-1



4. Functional diagram



Fig 1. Logic symbol

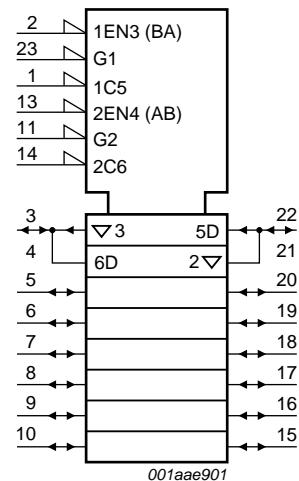


Fig 2. IEC logic symbol

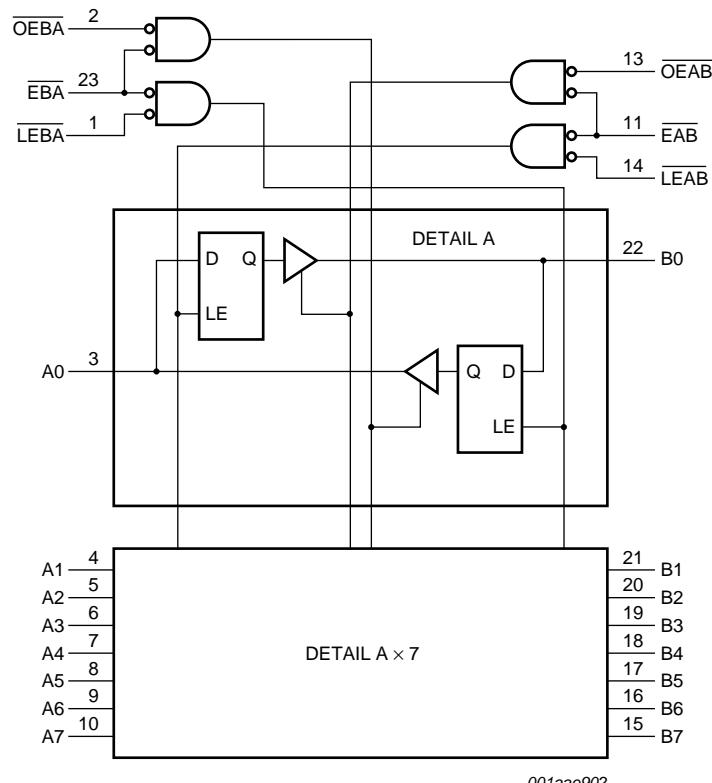


Fig 3. Logic diagram

5. Pinning information

5.1 Pinning

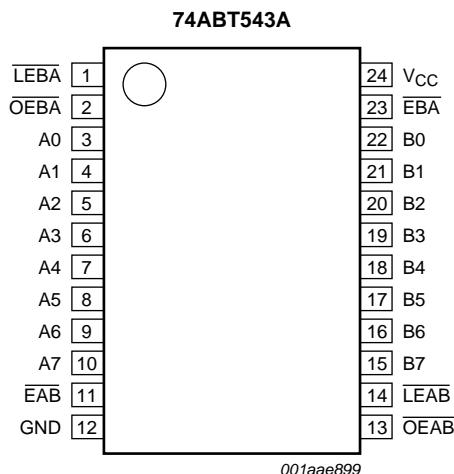


Fig 4. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
LEBA	1	B-to-A latch enable input (active LOW)
OEBA	2	B-to-A output enable input (active LOW)
A0 to A7	3, 4, 5, 6, 7, 8, 9, 10	data input or output
EAB	11	A-to-B enable input (active LOW)
GND	12	ground (0 V)
OEAB	13	A-to-B output enable input (active LOW)
LEAB	14	A-to-B latch enable input (active LOW)
B0 to B7	22, 21, 20, 19, 18, 17, 16, 15	data input or output
EBA	23	B-to-A enable input (active LOW)
V _{CC}	24	positive supply voltage

6. Functional description

6.1 Function table

Table 3. Function selection^[1]

Input			Output	Status	
OEXX	EXX	LEXX	An or Bn	Bn or An	
H	X	X	X	Z	disabled
X	H	X	X	Z	
L	↑	L	h	Z	disabled + latch
			I	Z	
L	L	↑	h	H	latch + display
			I	L	
L	L	L	H	H	transparent
			L	L	
L	L	H	X	NC	hold

[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition of $\overline{\text{LEXX}}$ or $\overline{\text{EXX}}$ (XX = AB or BA);

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition of $\overline{\text{LEXX}}$ or $\overline{\text{EXX}}$ (XX = AB or BA);

↑ = LOW-to-HIGH clock transition of $\overline{\text{LEXX}}$ or $\overline{\text{EXX}}$ (XX = AB or BA);

NC = no change;

X = don't care;

Z = high-impedance OFF-state.

6.2 Description

The 74ABT543A contains two sets of eight D-type latches, with separate control pins for each set.

Using data flow from A-to-B as an example, when the A-to-B enable ($\overline{\text{EAB}}$) input, the A-to-B latch enable ($\overline{\text{LEAB}}$) input and the A-to-B output enable ($\overline{\text{OEAB}}$) input are all LOW, the A-to-B path is transparent.

A subsequent LOW-to-HIGH transition of the $\overline{\text{LEAB}}$ signal puts the A data into the latches where it is stored and the B outputs no longer change with the A inputs. With $\overline{\text{EAB}}$ and $\overline{\text{OEAB}}$ both LOW, the 3-state B output buffers are active and display the data present at the outputs of the A latches.

Control of data flow from B-to-A is similar, but using the $\overline{\text{EBA}}$, $\overline{\text{LEBA}}$, and $\overline{\text{OEBA}}$ inputs.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
V _I	input voltage		[1] -1.2	+7.0	V
V _O	output voltage	output in OFF-state or HIGH-state	[1] -0.5	+5.5	V
I _{IK}	input clamping current	V _I < 0 V	-18	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	output in LOW-state	-	128	mA
T _j	junction temperature		[2] -	150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		4.5	-	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current		-	-	64	mA
Δt/ΔV	input transition rise and fall rate		0	-	10	ns/V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C

9. Static characteristics

Table 6. Static characteristics

Symbol	Parameter	Conditions	25 °C			Unit		
			Min	Typ	Max			
V _{IK}	input clamping voltage	V _{CC} = 4.5 V; I _{IK} = -18 mA	-1.2	-0.9	-	-1.2	-	V
V _{OH}	HIGH-level output voltage	V _I = V _{IL} or V _{IH}						
		V _{CC} = 4.5 V; I _{OH} = -3 mA	2.5	3.2	-	2.5	-	V
		V _{CC} = 5.0 V; I _{OH} = -3 mA	3.0	3.7	-	3.0	-	V
		V _{CC} = 4.5 V; I _{OH} = -32 mA	2.0	2.3	-	2.0	-	V
V _{OL}	LOW-level output voltage	V _{CC} = 4.5 V; I _{OL} = 64 mA; V _I = V _{IL} or V _{IH}	-	0.3	0.55	-	0.55	V
V _{OL(pu)}	power-up LOW-level output voltage	V _{CC} = 5.5 V; I _O = 1 mA; V _I = GND or V _{CC}	-	0.13	0.55	-	0.55	V

Table 6. Static characteristics ...continued

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		Unit
			Min	Typ	Max	Min	Max	
I _I	input leakage current	V _{CC} = 5.5 V; V _I = GND or 5.5 V OEAB, OEBA	-	±0.01	±1.0	-	±1.0	μA
		An, Bn	-	±5.0	±100	-	±100	μA
I _{OFF}	power-off leakage current	V _{CC} = 0.0 V; V _I or V _O ≤ 4.5 V	-	±5.0	±100	-	±100	μA
I _{O(pu/pd)}	power-up/power-down output current	V _{CC} = 2.1 V; V _O = 0.5 V; V _I = GND or V _{CC} ; OEAB, OEBA don't care	[1]	-	±5.0	±50	-	±50 μA
I _{OZ}	OFF-state output current	V _{CC} = 5.5 V; V _I = V _{IL} or V _{IH}						
		V _O = 2.7 V	-	5.0	50	-	50	μA
		V _O = 0.5 V	-	−5.0	−50	-	−50	μA
I _{LO}	output leakage current	HIGH-state; V _O = 5.5 V; V _{CC} = 5.5 V; V _I = GND or V _{CC}	-	5.0	50	-	50	μA
I _O	output current	V _{CC} = 5.5 V; V _O = 2.5 V	[2]	−180	−65	−40	−180	−40 mA
		V _{CC} = 5.5 V; V _I = GND or V _{CC}						
		outputs HIGH-state	-	110	250	-	250	μA
I _{CC}	supply current	outputs LOW-state	-	20	30	-	30	mA
		outputs disabled	-	110	250	-	250	μA
		per input pin; V _{CC} = 5.5 V; one input pin at 3.4 V, other inputs at V _{CC} or GND	[3]	-	0.3	1.5	-	1.5 mA
C _I	input capacitance	V _I = 0 V or V _{CC}	-	4	-	-	-	pF
C _{I/O}	input/output capacitance	outputs disabled; V _O = 0 V or V _{CC}	-	7	-	-	-	pF

[1] This parameter is valid for any V_{CC} between 0 V and 2.1 V, with a transition time of up to 10 ms. From V_{CC} = 2.1 V to V_{CC} = 5 V ± 10 %, a transition time of up to 100 μs is permitted.

[2] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

[3] This is the increase in supply current for each input at 3.4 V.

10. Dynamic characteristics

Table 7. Dynamic characteristics

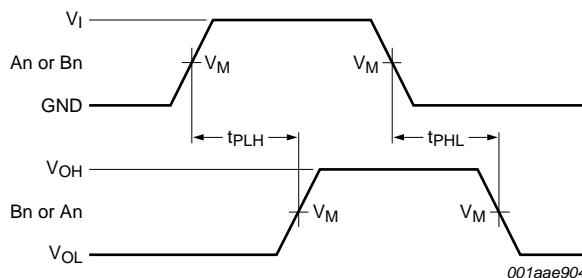
GND = 0 V; for test circuit, see [Figure 10](#).

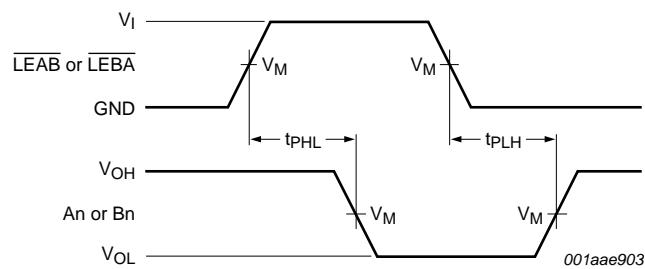
Symbol	Parameter	Conditions	25 °C; V _{CC} = 5.0 V			−40 °C to +85 °C; V _{CC} = 5.0 V ± 0.5 V		Unit
			Min	Typ	Max	Min	Max	
t _{PLH}	LOW to HIGH propagation delay	An to Bn or Bn to An; see Figure 5 LEBA to An or LEAB to Bn; see Figure 6	1.0	2.9	4.5	1.0	5.2	ns
			1.0	3.4	5.1	1.0	6.2	ns
t _{PHL}	HIGH to LOW propagation delay	An to Bn or Bn to An; see Figure 5 LEBA to An or LEAB to Bn; see Figure 6	1.9	3.6	5.2	1.9	5.7	ns
			2.1	4.3	6.0	2.1	6.7	ns
t _{PZH}	OFF-state to HIGH propagation delay	OEBA to An, OEAB to Bn; see Figure 7 EBA to An, EAB to Bn; see Figure 7	1.0	3.2	5.1	1.0	6.2	ns
			1.0	3.4	5.1	1.0	6.2	ns

Table 7. Dynamic characteristics ...continuedGND = 0 V; for test circuit, see [Figure 10](#).

Symbol	Parameter	Conditions	25 °C; V _{CC} = 5.0 V			−40 °C to +85 °C; V _{CC} = 5.0 V ± 0.5 V		Unit
			Min	Typ	Max	Min	Max	
t _{PZL}	OFF-state to LOW propagation delay	OEBA to An, \overline{OEAB} to Bn; see Figure 8	2.0	4.3	5.9	2.0	6.6	ns
		EBA to An, \overline{EAB} to Bn; see Figure 8	2.0	4.4	6.1	2.0	6.8	ns
t _{PHZ}	HIGH to OFF-state propagation delay	OEBA to An, \overline{OEAB} to Bn; see Figure 7	2.0	4.0	5.7	2.0	6.2	ns
		EBA to An, \overline{EAB} to Bn; see Figure 7	2.0	3.6	5.4	2.0	5.9	ns
t _{PLZ}	LOW to OFF-state propagation delay	OEBA to An, \overline{OEAB} to Bn; see Figure 8	1.0	3.0	4.6	1.0	5.0	ns
		EBA to An, \overline{EAB} to Bn; see Figure 8	1.0	3.0	4.6	1.0	5.0	ns
t _{su(H)}	set-up time HIGH	An to \overline{LEAB} , Bn to \overline{LEBA} ; see Figure 9	2.5	1.0	-	2.5	-	ns
		An to \overline{EAB} , Bn to \overline{EBA} ; see Figure 9	3.5	1.3	-	3.5	-	ns
t _{su(L)}	set-up time LOW	An to \overline{LEAB} , Bn to \overline{LEBA} ; see Figure 9	3.0	1.4	-	3.0	-	ns
		An to \overline{EAB} , Bn to \overline{EBA} ; see Figure 9	3.0	1.4	-	3.0	-	ns
t _{h(H)}	hold time HIGH	\overline{LEAB} to An, \overline{LEBA} to Bn; see Figure 9	+0.5	-0.8	-	0.5	-	ns
		EAB to An, \overline{EBA} to Bn; see Figure 9	+0.5	-0.8	-	0.5	-	ns
t _{h(L)}	hold time LOW	\overline{LEAB} to An, \overline{LEBA} to Bn; see Figure 9	+0.5	-0.6	-	0.5	-	ns
		EAB to An, \overline{EBA} to Bn; see Figure 9	+0.5	-0.6	-	0.5	-	ns
t _{WL}	pulse width LOW	latch enable; see Figure 9	3.5	1.0	-	3.5	-	ns

11. Waveforms

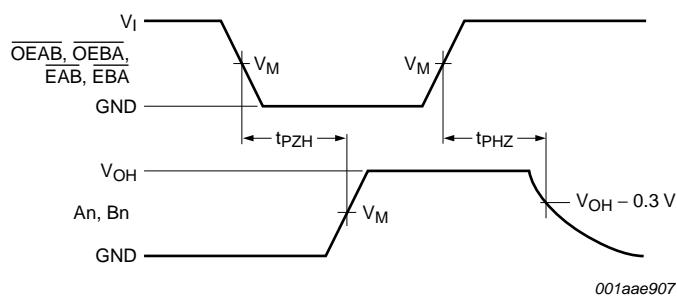
 $V_M = 1.5$ V. V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.**Fig 5. Propagation delay input (An, Bn) to output (Bn, An)**



$V_M = 1.5\text{ V}$.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

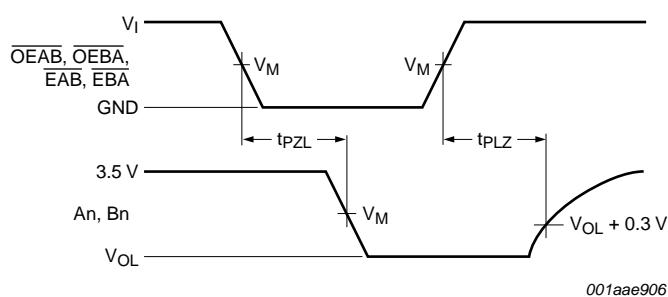
Fig 6. Propagation delay latch enable (\overline{LEAB} , \overline{LEBA}) to output (An , Bn)



$V_M = 1.5\text{ V}$.

V_{OH} is a typical voltage output level that occurs with the output load.

Fig 7. Propagation delay 3-state output enable to HIGH-level and output disable from HIGH-level



$V_M = 1.5\text{ V}$.

V_{OL} is a typical voltage output level that occurs with the output load.

Fig 8. Propagation delay 3-state output enable to LOW-level and output disable from LOW-level

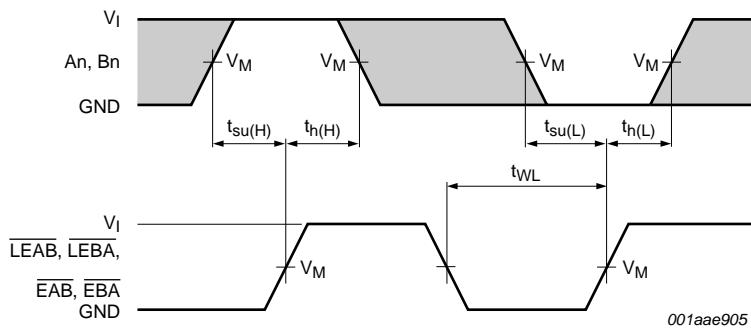
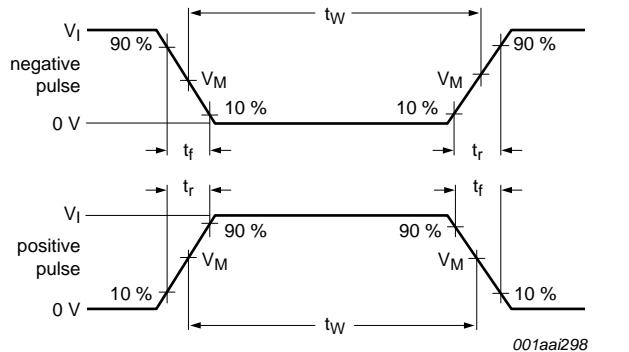


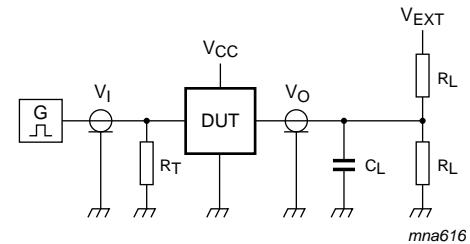
Fig 9. Data set-up and hold times and latch enable pulse width



a. Input pulse definition

Test data is given in [Table 8](#).

Test circuit definitions:

 R_L = Load resistance. C_L = Load capacitance including jig and probe capacitance. R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator. V_{EXT} = Test voltage for switching times.

b. Test circuit

Fig 10. Load circuitry for switching times

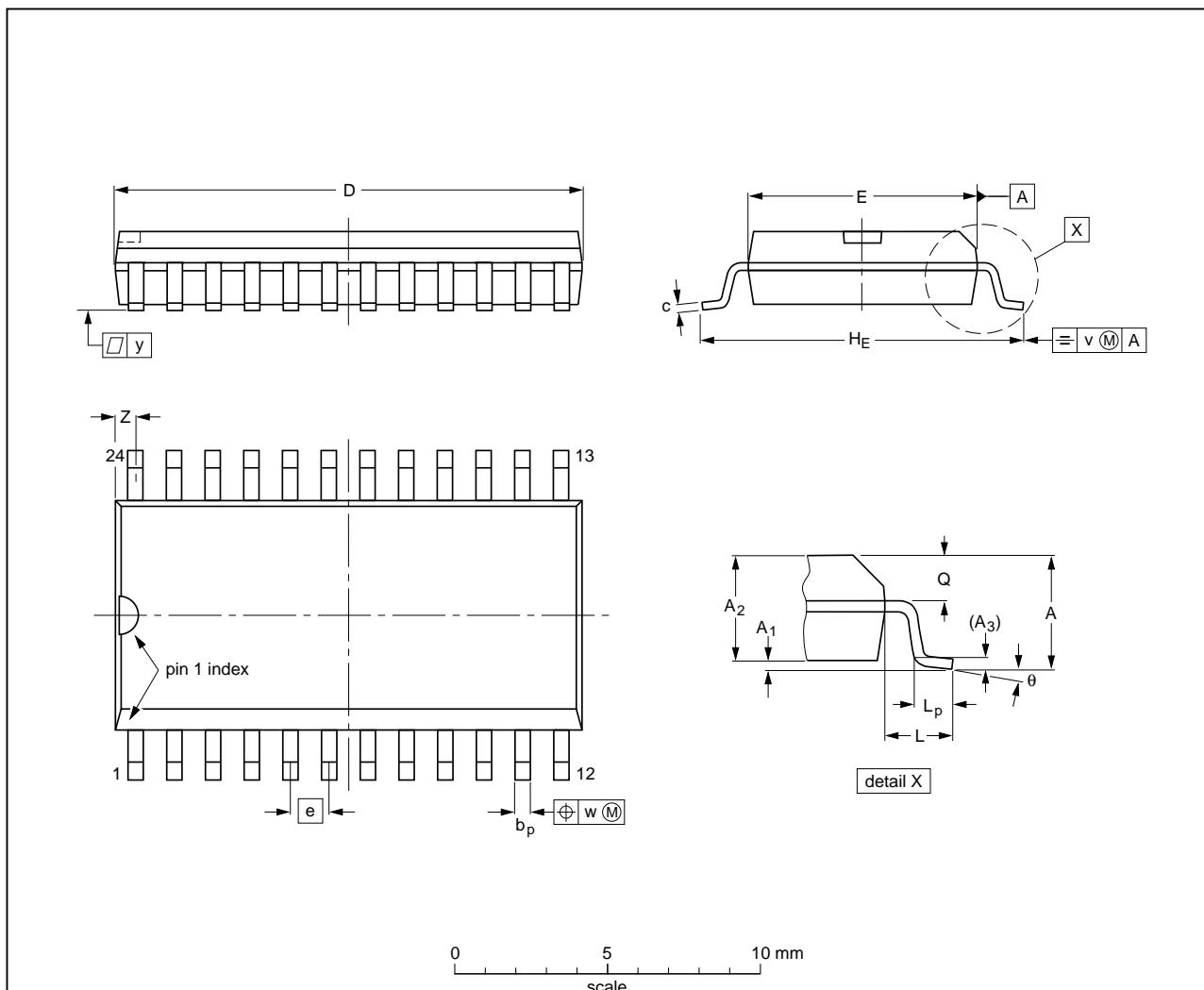
Table 8. Test data

Input				Load		V_{EXT}			
V_I	f_I	t_w	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}	
3.0 V	1 MHz	500 ns	$\leq 2.5 \text{ ns}$	50 pF	500 Ω	open	open	7.0 V	

12. Package outline

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	2.65 0.1	0.3 2.25	2.45	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT137-1	075E05	MS-013			-99-12-27 03-02-19

Fig 11. Package outline SOT137-1 (SO24)

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm

SOT340-1

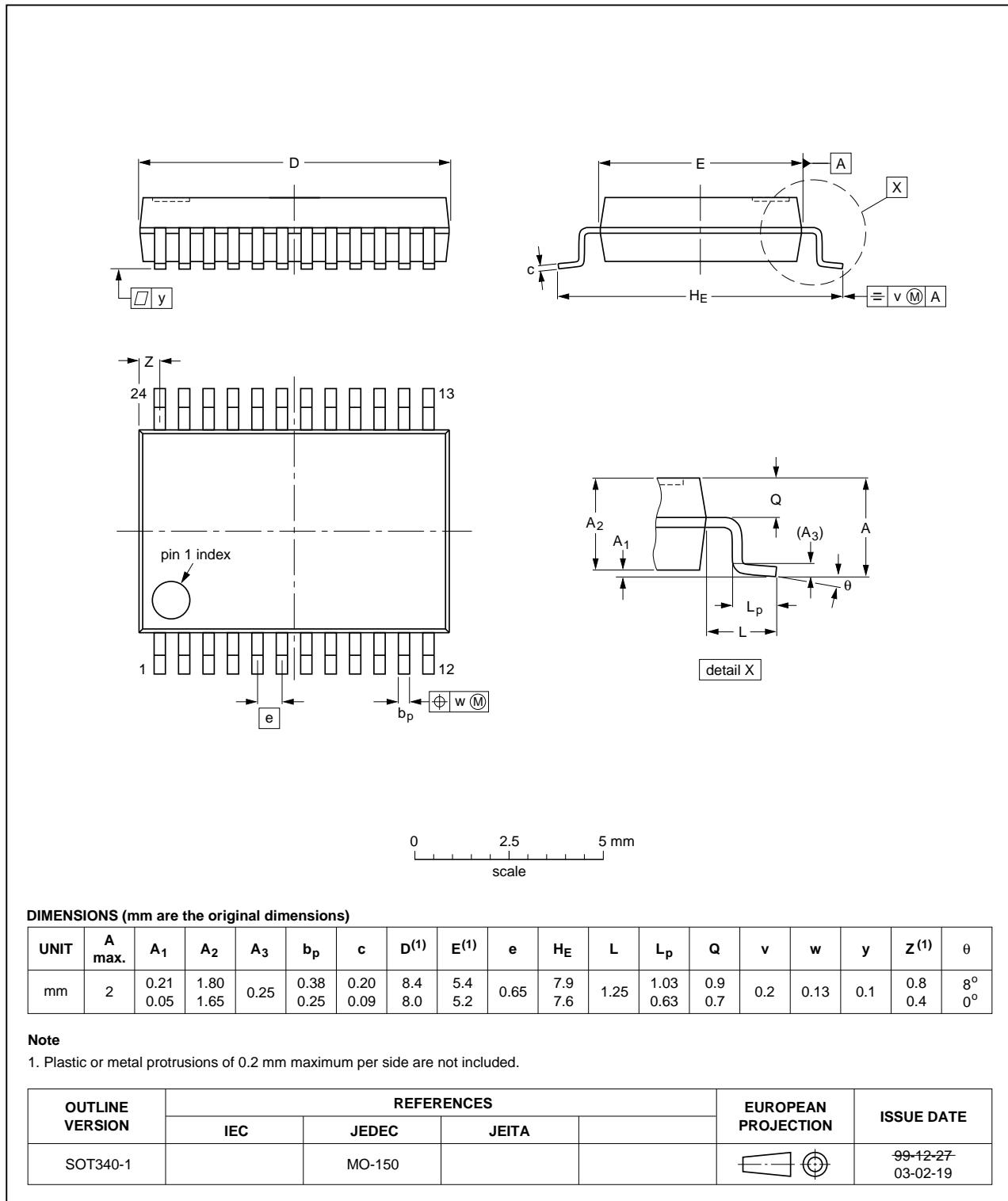


Fig 12. Package outline SOT340-1 (SSOP24)

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1

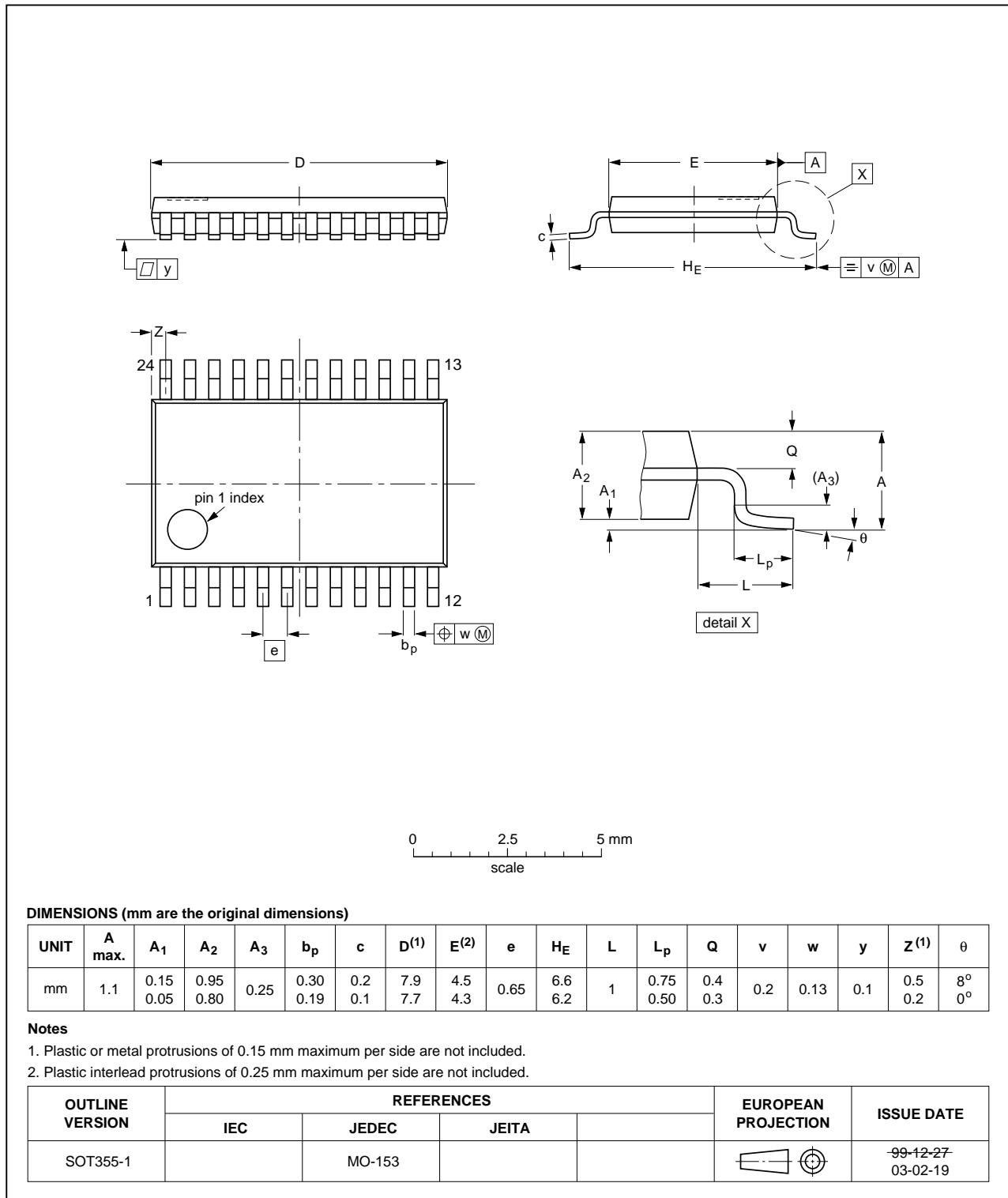


Fig 13. Package outline SOT355-1 (TSSOP24)

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ABT543A v.5	20111103	Product data sheet	-	74ABT543A v.4
Modifications:		• Legal pages updated		
74ABT543A v.4	20100507	Product data sheet	-	74ABT543A v.3
74ABT543A v.3	20100126	Product data sheet	-	74ABT543A v.2
74ABT543A v.2	19980924	Product specification	-	74ABT543A v.1
74ABT543A v.1	19950419	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

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